

CDBDSC5650-G

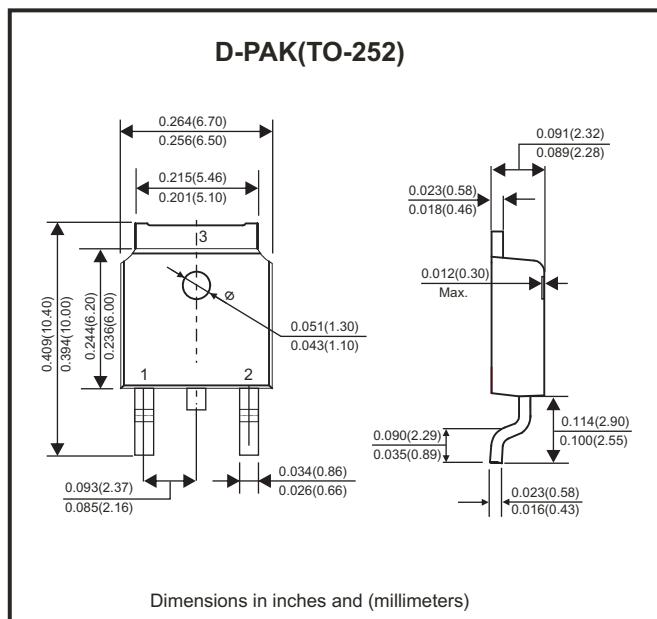
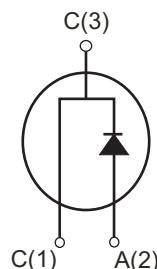
Reverse Voltage: 650 V
Forward Current: 5 A
RoHS Device



Features

- Rated to 650V at 5 Amps
- Short recovery time
- High speed switching possible
- High frequency operation.
- High temperature operation.
- Temperature independent switching behaviour.
- Positive temperature coefficient on VF

Circuit Diagram



Maximum Ratings (at $T_A=25^\circ\text{C}$, unless otherwise noted)

| Parameter | Conditions | Symbol | Value | Unit |
|---|--|-----------------|-----------------|---------------------------|
| Repetitive peak reverse voltage | | V_{RRM} | 650 | V |
| Surge peak reverse voltage | | V_{RSM} | 650 | V |
| DC blocking voltage | | V_{DC} | 650 | V |
| Continuous forward current | $T_c = 25^\circ\text{C}$ $T_c = 135^\circ\text{C}$ $T_c = 160^\circ\text{C}$ | I_F | 21.5 10 5 | A |
| Repetitive peak forward surge current | $T_c = 25^\circ\text{C}$, $t_p = 10\text{ms}$ Half sine wave, $D = 0.3$ | I_{FRM} | 40 | A |
| Non-repetitive peak forward surge current | $T_c = 25^\circ\text{C}$, $t_p = 10\text{ms}$ Half sine wave | I_{FSM} | 80 | A |
| Power dissipation | $T_c = 25^\circ\text{C}$ $T_c = 110^\circ\text{C}$ | P_{TOT} | 85.8 37.2 | W |
| Typical thermal resistance | Junction to case | $R_{\theta JC}$ | 1.748 | $^\circ\text{C}/\text{W}$ |
| Operating junction temperature range | | T_J | -55 ~ +175 | $^\circ\text{C}$ |
| Storage temperature range | | T_{STG} | -55 ~ +175 | $^\circ\text{C}$ |

Electrical Characteristics (at $T_A=25^\circ\text{C}$, unless otherwise noted)

| Parameter | Conditions | Symbol | Min. | Typ. | Max. | Unit |
|-------------------------|--|--------|------|------|------|---------------|
| Forward voltage | $I_F = 5\text{A}, T_J = 25^\circ\text{C}$ | V_F | | 1.35 | 1.7 | V |
| | $I_F = 5\text{A}, T_J = 175^\circ\text{C}$ | | | 1.55 | 2.5 | |
| Reverse current | $V_R = 650\text{V}, T_J = 25^\circ\text{C}$ | I_R | | 10 | 100 | μA |
| | $V_R = 650\text{V}, T_J = 175^\circ\text{C}$ | | | 15 | 200 | |
| Total capacitive charge | $V_R = 400\text{V}, T_J = 150^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V) dV$ | Q_C | | 23 | | nC |
| Total capacitance | $V_R = 0\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$ | C | | 424 | 434 | pF |
| | $V_R = 200\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$ | | | 44 | 45 | |
| | $V_R = 400\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$ | | | 42.5 | 43 | |

RATING AND CHARACTERISTIC CURVES (CDBDSC5650-G)

Fig.1 - Forward Characteristics

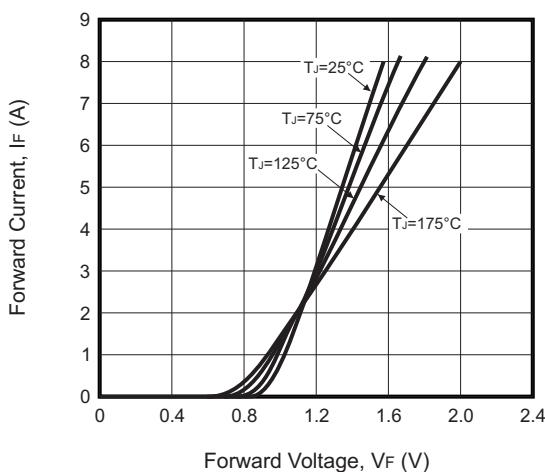


Fig.2 - Reverse Characteristics

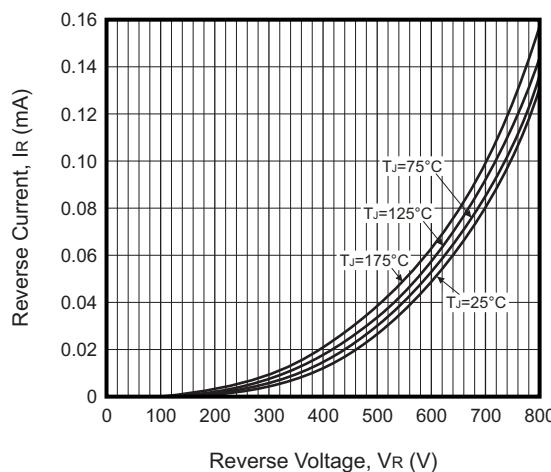


Fig.3 - Current Derating

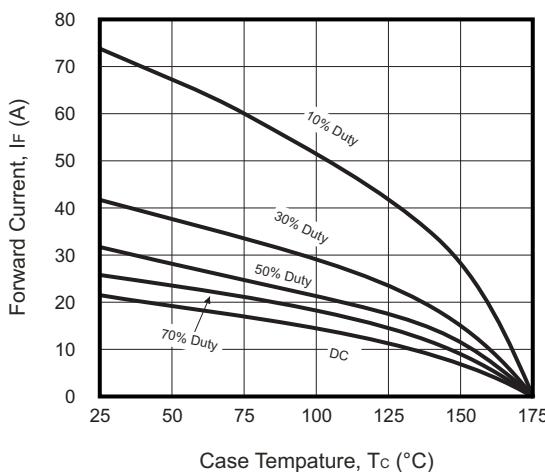


Fig.4 - Capacitance vs. Reverse Voltage

